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SEMICONDUCTOR

November 2013

FQD7N20L N-Channel QFET[®] MOSFET 200 V, 5.5 A, 750 mΩ

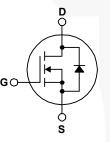
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- 5.5 A, 200 V, $R_{DS(on)}$ = 750 m Ω (Max.) @ V_{GS} = 10 V, I_D = 2.75 A
- Low Gate Charge (Typ. 6.8 nC)
- Low Crss (Typ. 8.5 pF)
- RoHS Compliant
- · Low Level Gate Drive Requirement Allowing Direct Operating from Logic Drivers





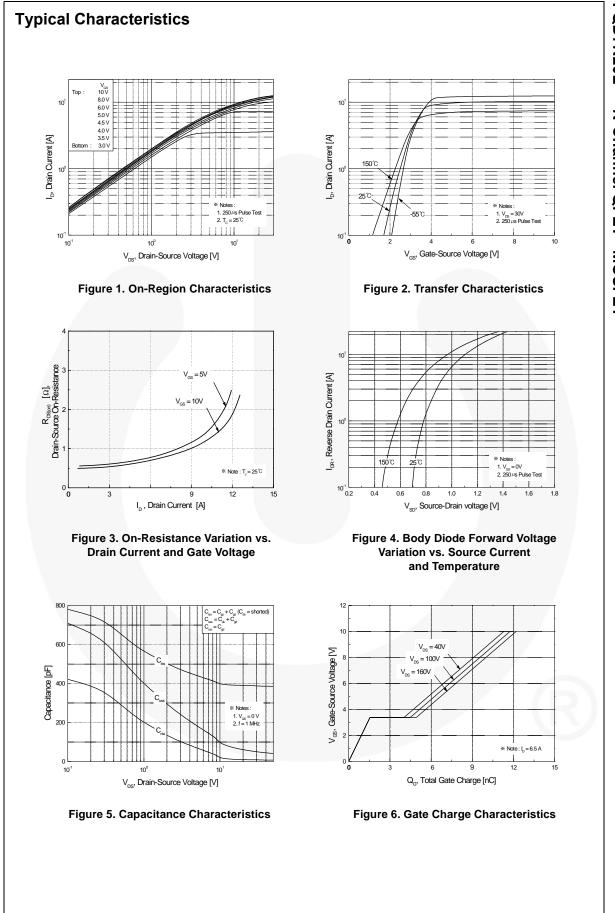
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

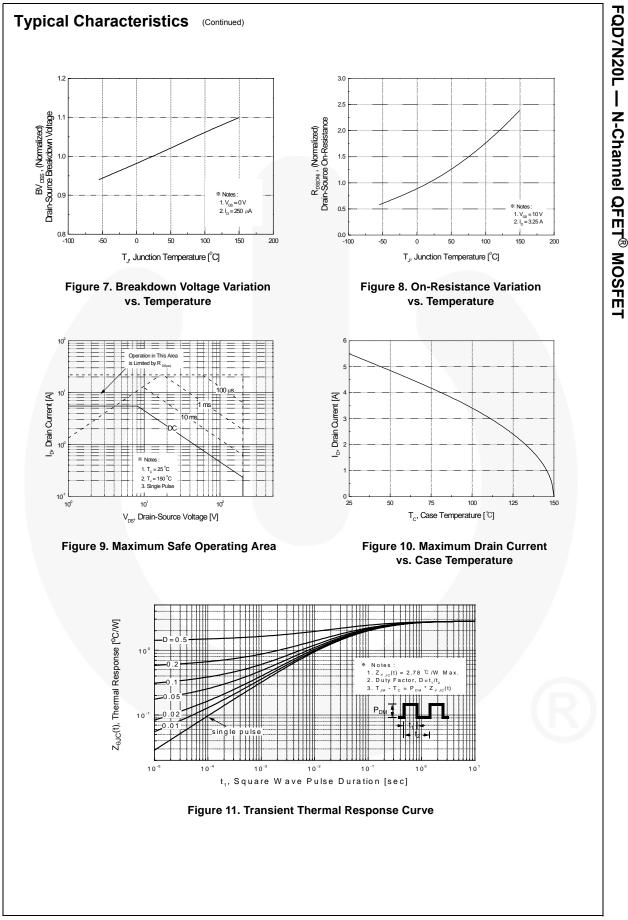
Symbol	Parameter	FQD7N20LTM	Unit
V _{DSS}	Drain-Source Voltage	200	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)	5.5	А
	- Continuous (T _C = 100°C)	3.48	A
I _{DM}	Drain Current - Pulsed (Note 1)	22	A
V _{GSS}	Gate-Source Voltage	± 20	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	73	mJ
I _{AR}	Avalanche Current (Note 1)	5.5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *	2.5	W
	Power Dissipation (T _C = 25°C)	45	W
	- Derate above 25°C	0.36	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C

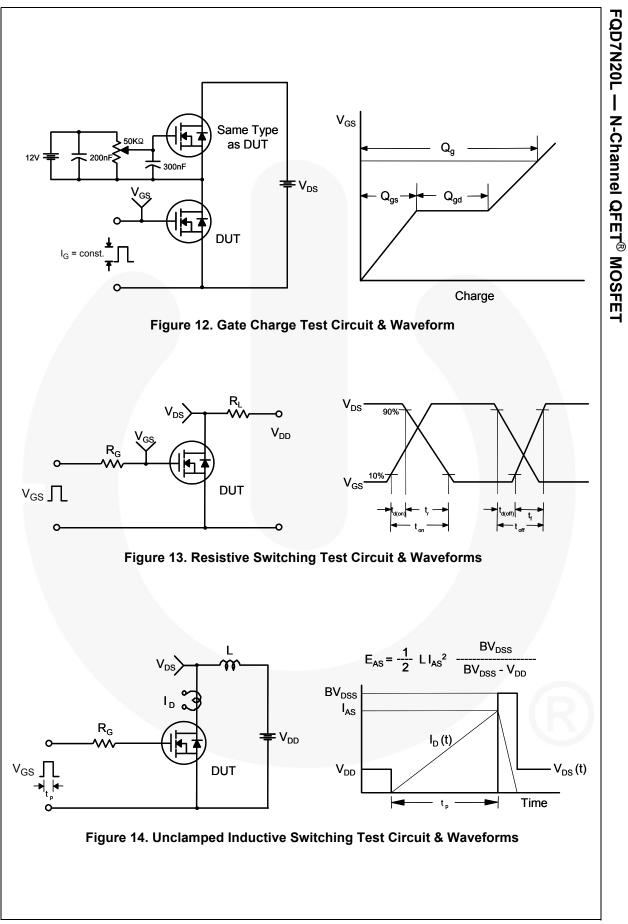
Thermal Characteristics

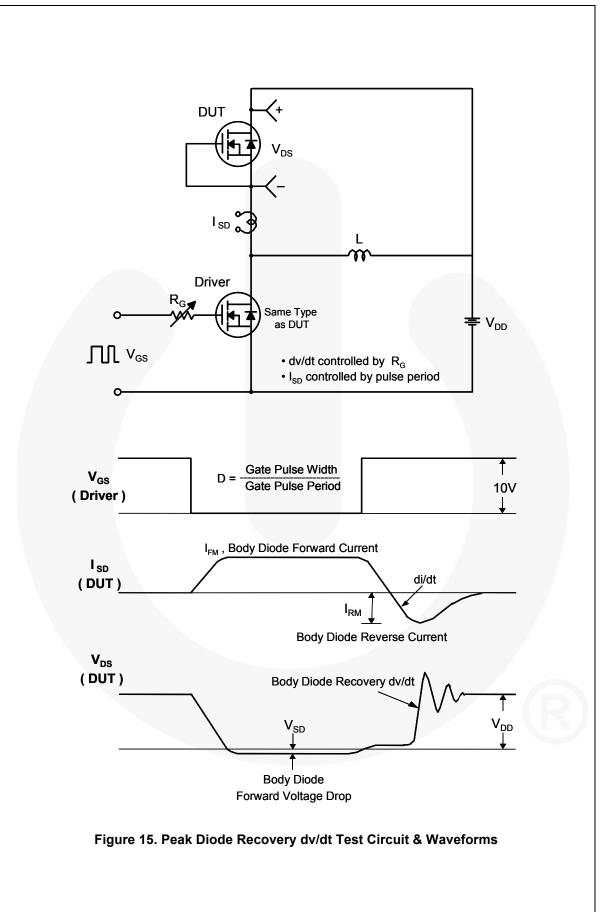
Symbol	Parameter	FQD7N20LTM	Unit	
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	2.78		
Р	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50		

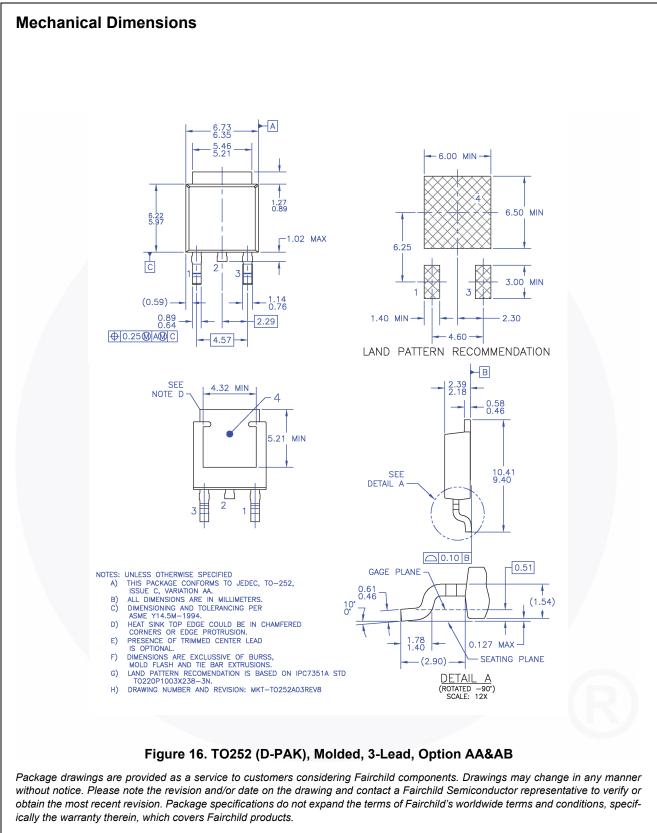
Part Number FQD7N20LTM		Top Mark	Pack	age	Packing Method Re		Size	Tape Width		Quantity 2500 units	
		FQD7N20L	DP	DPAK Tape a		eel 330 mm		16 mi	m 2		
ectri	cal Cha	racteristics	T _C = 25°0	C unless ot	nerwise noted.						
Symbol		Parameter	-		Test Condition	s	Min.	Тур.	Max.	Unit	
Off Cha	aracterist	ics									
BV _{DSS}	Drain-Sou	ain-Source Breakdown Voltage		V _{GS} =	0 V, I _D = 250 μA		200			V	
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu\text{A}$, Referenced to 25°C				0.17		V/°C		
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} = 200 V, V _{GS} = 0 V					1	μA		
			V _{DS} = 160 V, T _C = 125°C					10	μΑ		
I _{GSSF}	Gate-Body Leakage Current, Forward		V_{GS} = 20 V, V_{DS} = 0 V					100	nA		
I _{GSSR}	Gate-Bod	y Leakage Current,	Reverse	V _{GS} =	-20 V, V _{DS} = 0 V				-100	nA	
On Cha	aracterist	ics									
V _{GS(th)}	Gate Thre	shold Voltage		-	V _{GS} , I _D = 250 μA		1.0		2.0	V	
R _{DS(on)}	Static Drain-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.75 \text{ A}$				0.59	0.75	Ω		
~	On-Resist		_		5 V, I _D = 2.75 A 30 V, I _D = 2.75 A			0.62	0.78	0	
9 _{FS}	Forward	ransconductance	_	V _{DS} =	$30 \text{ V}, \text{ I}_{\text{D}} = 2.75 \text{ A}$			5.6		S	
Dynam	ic Chara	cteristics									
C _{iss}	Input Cap	acitance		V _{DS} =	25 V, V _{GS} = 0 V, MHz			390	500	pF	
C _{oss}	Output Ca	apacitance		f = 1.0				55	70	pF	
C _{rss}	Reverse 7	Fransfer Capacitance	e					8.5	11	pF	
Switch	ing Char	acteristics									
t _{d(on)}		Delay Time	_	V -				12	35	ns	
t _r	Turn-On F	Rise Time	_	$V_{DD} =$ $R_G = 2$	100 V, I _D = 6.5 A,			125	260	ns	
t _{d(off)}	Turn-Off	Delay Time	-	$r_G - 2$	10 12	(Note 4)		20	50	ns	
t _f	Turn-Off F	all Time						65	140	ns	
Q _g	Total Gate	e Charge		Vpe =	160 V, I _D = 6.5 A,			6.8	9.0	nC	
Q _{gs}	Gate-Sou	rce Charge		V _{GS} =	-	(Note 4)		1.6		nC	
Q _{gd}	Gate-Drai	n Charge						3.4		nC	
									1		
Drain-S		ode Characteri				S			5.5	A	
I _{SM}		Pulsed Drain-Source							22	A	
V _{SD}		Irce Diode Forward							1.5	V	
t _{rr}		Recovery Time	, onage	$V_{GS} = 0 V, I_S = 5.5 A$ $V_{GS} = 0 V, I_S = 6.5 A,$			110		ns		
		Recovery Charge			$t = 100 \text{ A}/\mu \text{s}$			0.44		μC	
Q _{rr}								0.11		μΟ	











Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

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FQD7N20L — N-Channel QFET[®] MOSFET



No Identification Needed

Obsolete

Full Production

Not In Production

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Rev. 166

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